

Nanochannel fabrication based on double patterning with hydrogen silsesquioxane

Kenneth Diest, Russell Goodman and Mordechai Rothschild

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Da-Bin Jeon, Min-Ki Ryu, Chun-Won Byun, Jong-Heon Yang, Chi-Sun Hwang and Sung-Min Yoon

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Alexander Palov, Tatiana V. Rakhimova, Mikhail B. Krishtab and Mikhail R. Baklanov

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Takashi Yamazaki, Takashi Kato, Taiki Uemura, Hideya Matsuyama, Yoko Tada, Kazutoshi Yamazaki, Takeshi Soeda, Toyoo Miyajima and Yuji Kataoka

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Norman R. Fong, Pierre Berini and Niall Tait

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Oxide structure-dependent interfacial layer defects of HfAlO/SiO₂/Si stack analyzed by conductance method

Yi Ming Ding and Durgamadhab Misra

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Paul B. Rago and John E. Ayers

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Seonghoon Jeong and Hyunsoo Kim

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Aaron G. Lind, Henry L. Aldridge Jr., Cory C. Bomberger, Christopher Hatem, Joshua M. O. Zide and Kevin S. Jones

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Andreas Westlund, Per-Åke Nilsson, Paul Sangaré, Guillaume Ducournau, Christophe Gaquière, Ludovic Desplanque, Xavier Wallart and Jan Grahn

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